



Figure 1 (a) Schematic cross-section of the device structure, (b) Simulated trajectory of electron beam across material using CASINO, (c) Normalized Voc as a function of electron fluence and displacement damage dose (d) Dark I-V curves before and after irradiation, (e) and (f) External Quantum Efficiency of InGaAsP/InGaAs double-junction and InGaAs single-junction solar cell before (black curves) and after irradiation (colored curves), respectively, at different electron fluence levels.